

**NIKO-SEM**

# N-Channel Enhancement Mode Field Effect Transistor

**PE5E4BA**  
PDFN 3x3P  
Halogen-Free & Lead-Free

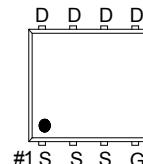
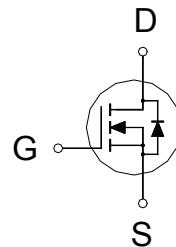


## PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(on)}$	$I_D$
30V	9.5mΩ	31A

## Features

- Pb-Free, Halogen Free and RoHS compliant.
- Low  $R_{DS(on)}$  to Minimize Conduction Losses.
- Ohmic Region Good  $R_{DS(on)}$  Ratio.
- Optimized Gate Charge to Minimize Switching Losses.



G. GATE  
D. DRAIN  
S. SOURCE

## Applications

- Protection Circuits Applications.
- Logic/Load Switch Circuits Applications.

## ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMITS	UNITS
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 25$	V
Continuous Drain Current <sup>3</sup>	$I_D$	31	A
$T_C = 100^\circ\text{C}$		19	
Pulsed Drain Current <sup>1</sup>	$I_{DM}$	90	A
Continuous Drain Current	$I_D$	10	
$T_A = 70^\circ\text{C}$		8	
Avalanche Current	$I_{AS}$	22	
Avalanche Energy	$E_{AS}$	24	mJ
Power Dissipation	$P_D$	18	W
$T_C = 100^\circ\text{C}$		7	
Power Dissipation	$P_D$	1.7	W
$T_A = 70^\circ\text{C}$		1.1	
Operating Junction & Storage Temperature Range	$T_j, T_{stg}$	-55 to 150	°C

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**THERMAL RESISTANCE RATINGS**

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient <sup>2</sup>	Steady-State	$R_{\theta JA}$		70	$^{\circ}\text{C} / \text{W}$
Junction-to-Case	Steady-State	$R_{\theta JC}$		7	

<sup>1</sup>Pulse width limited by maximum junction temperature.<sup>2</sup>The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^{\circ}\text{C}$ .<sup>3</sup>Package limitation current is 27A.**ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ , Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(\text{BR})DSS}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	30			V
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.3	2	2.3	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{V}, V_{GS} = \pm 25\text{V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$			1	$\mu\text{A}$
		$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}, T_J = 55^{\circ}\text{C}$			10	
Drain-Source On-State Resistance <sup>1</sup>	$R_{DS(\text{ON})}$	$V_{GS} = 4.5\text{V}, I_D = 8.8\text{A}$		14.3	17	$\text{m}\Omega$
		$V_{GS} = 10\text{V}, I_D = 10\text{A}$		7.5	9.5	
Forward Transconductance <sup>1</sup>	$g_{fs}$	$V_{DS} = 5\text{V}, I_D = 10\text{A}$		28		S
<b>DYNAMIC</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 15\text{V}, f = 1\text{MHz}$		530		pF
Output Capacitance	$C_{oss}$			160		
Reverse Transfer Capacitance	$C_{rss}$			90		
Gate Resistance	$R_g$	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		2.7		$\Omega$
Total Gate Charge <sup>2</sup>	$Q_g$	$V_{DS} = 15\text{V}, V_{GS} = 10\text{V}, I_D = 10\text{A}$		12		nC
				6.7		
Gate-Source Charge <sup>2</sup>	$Q_{gs}$			1.5		
Gate-Drain Charge <sup>2</sup>	$Q_{gd}$			4.3		
Turn-On Delay Time <sup>2</sup>	$t_{d(on)}$			18		
Rise Time <sup>2</sup>	$t_r$		$V_{DS} = 15\text{V}, I_D \geq 10\text{A}, V_{GS} = 10\text{V}, R_{\text{GEN}} = 6\Omega$	16		
Turn-Off Delay Time <sup>2</sup>	$t_{d(off)}$			35		nS
Fall Time <sup>2</sup>	$t_f$			17		

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**SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T<sub>J</sub> = 25 °C)**

Continuous Current	I <sub>S</sub>			15	A
Forward Voltage <sup>1</sup>	V <sub>SD</sub>	I <sub>F</sub> = 10A, V <sub>GS</sub> = 0V		1.2	V
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 10A, dI <sub>F</sub> /dt = 100A / μS	15		nS
Reverse Recovery Charge	Q <sub>rr</sub>		5		nC

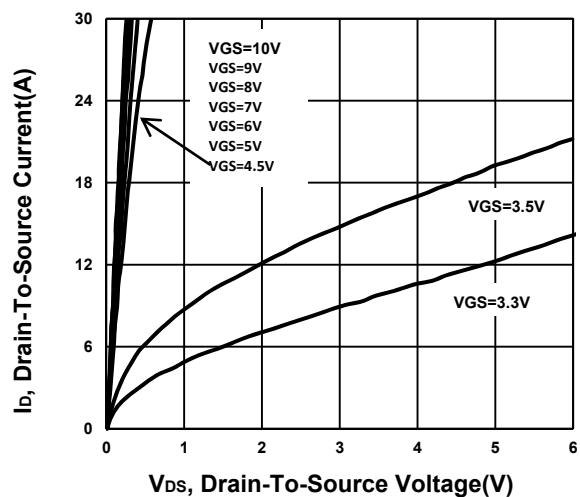
<sup>1</sup>Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.<sup>2</sup>Independent of operating temperature.

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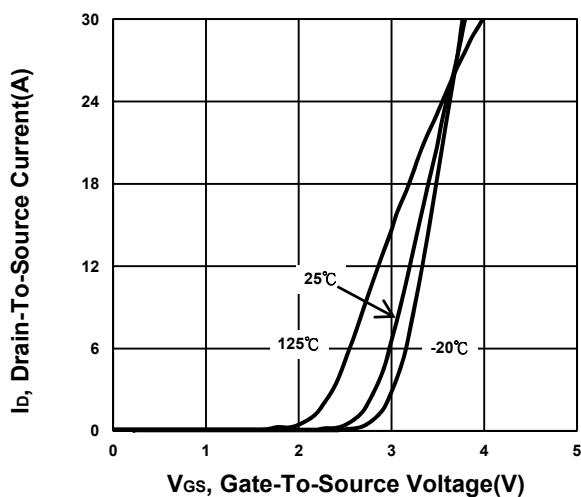
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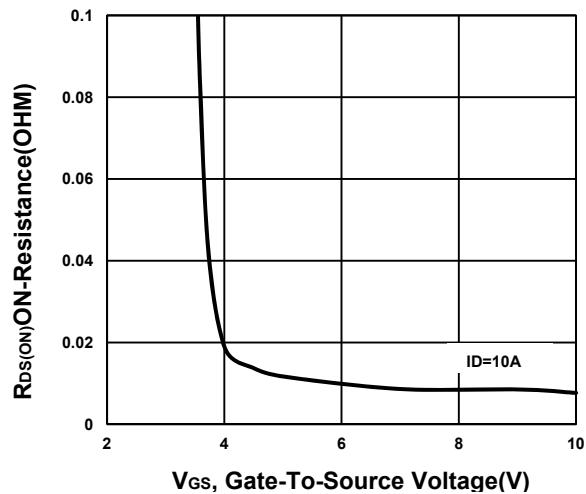
**Output Characteristics**



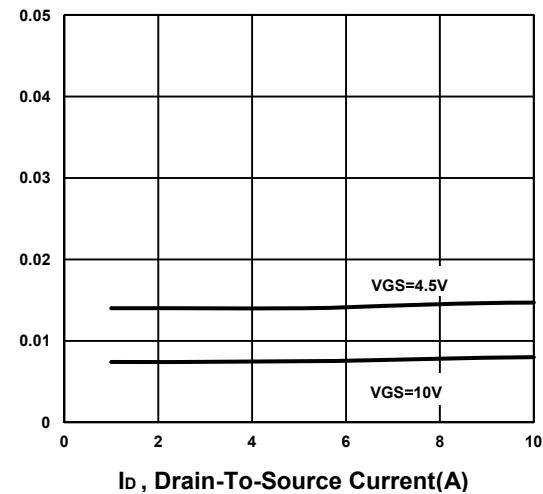
**Transfer Characteristics**



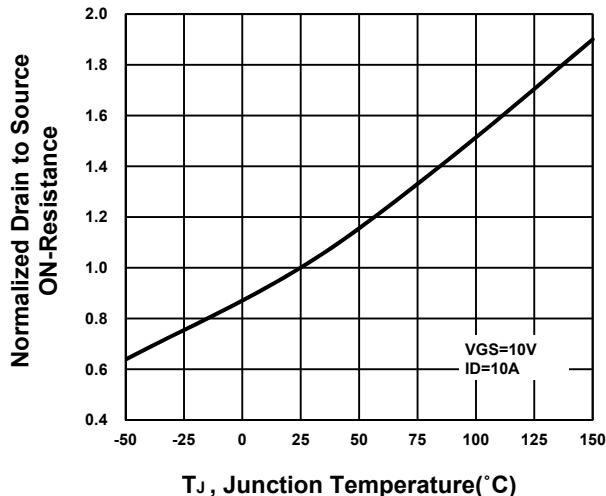
**On-Resistance VS Gate-To-Source**



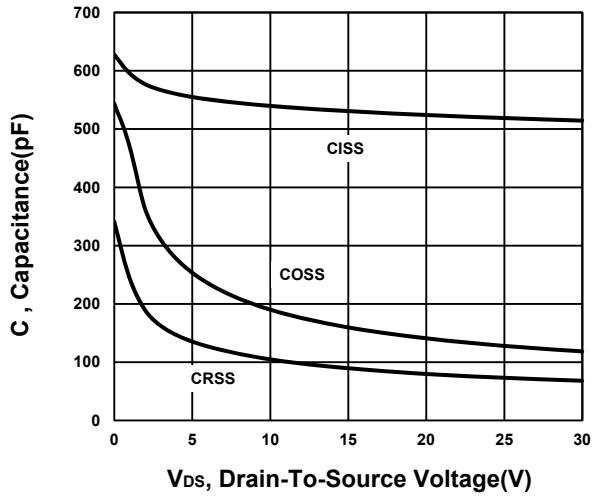
**On-Resistance VS Drain Current**



**On-Resistance VS Temperature**



**Capacitance Characteristic**

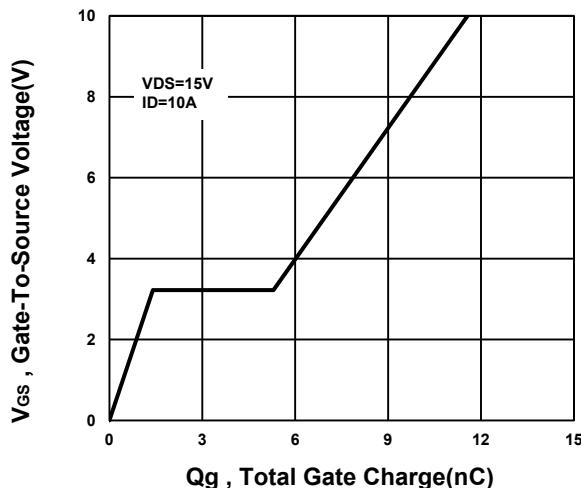


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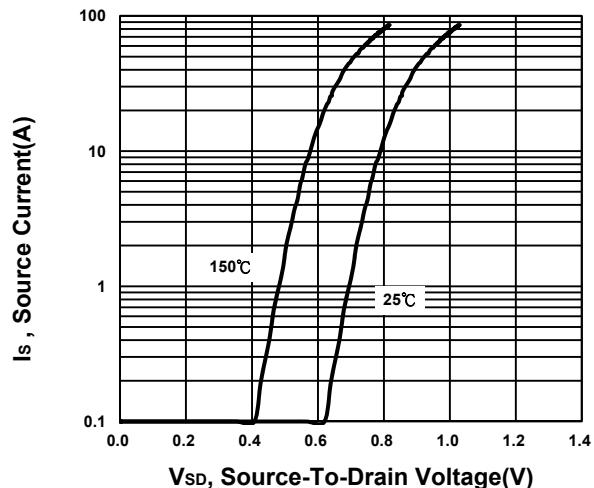
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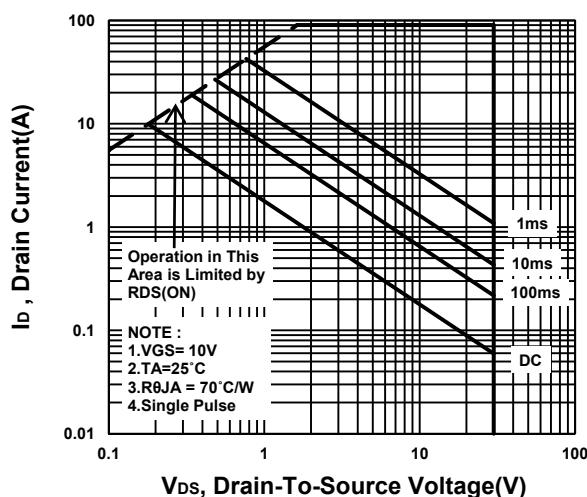
**Gate charge Characteristics**



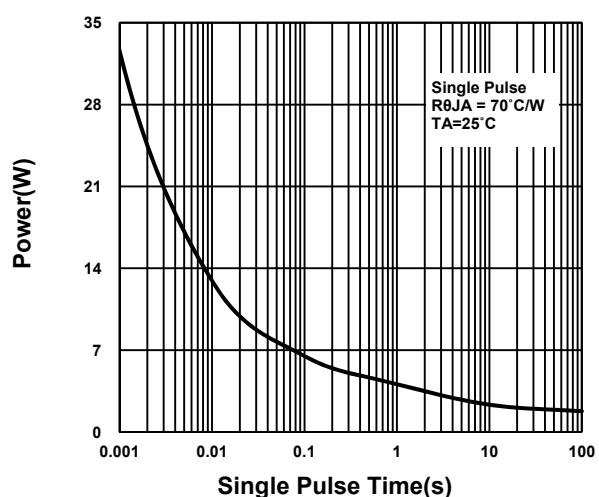
**Source-Drain Diode Forward Voltage**



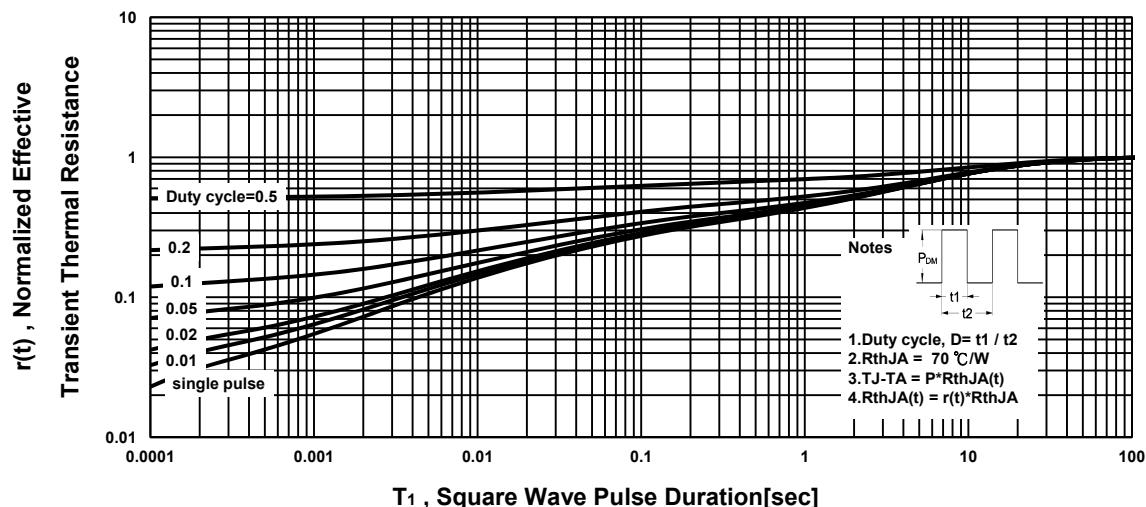
**Safe Operating Area**



**Single Pulse Maximum Power Dissipation**



**Transient Thermal Response Curve**



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